

650V GaN FET PQFN Series

Description

The TP65H150LSG 650V, 150mΩ Gallium Nitride (GaN) FET is a normally-off device. It combines state-of-the-art high voltage GaN HEMT and low voltage silicon MOSFET technologies—offering superior reliability and performance.

Transphorm GaN offers improved efficiency over silicon, through lower gate charge, lower crossover loss, and smaller reverse recovery charge.

Related Literature

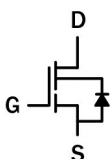
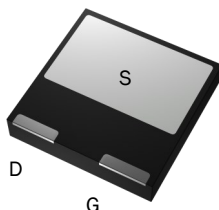
- [AN0009](#): Recommended External Circuitry for GaN FETs
- [AN0003](#): Printed Circuit Board Layout and Probing
- [AN0010](#): Paralleling GaN FETs

Ordering Information

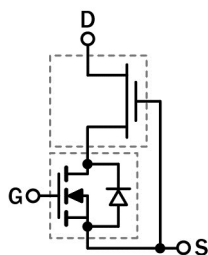
Part Number	Package	Package Configuration
TP65H150LSG	8 x 8mm PQFN	Source

* Add “-TR” suffix for tape and reel

TP65H150LSG
8x8 PQFN
(bottom view)



Cascode Schematic Symbol



Cascode Device Structure

Features

- JEDEC qualified GaN technology
- Dynamic $R_{DS(on)eff}$ production tested
- Robust design, defined by
 - Intrinsic lifetime tests
 - Wide gate safety margin
 - Transient over-voltage capability
- Very low Q_{RR}
- Reduced crossover loss
- RoHS compliant and Halogen-free packaging

Benefits

- Improves efficiency/operation frequencies over Si
- Enables AC-DC bridgeless totem-pole PFC designs
 - Increased power density
 - Reduced system size and weight
 - Overall lower system cost
- Easy to drive with commonly-used gate drivers
- GSD pin layout improves high speed design

Applications

- Datacom
- Broad industrial
- PV inverter
- Servo motor

Key Specifications

V_{DSS} (V)	650
$V_{(TR)DSS}$ (V)	800
$R_{DS(on)eff}$ (mΩ) max*	180
Q_{RR} (nC) typ	44
Q_G (nC) typ	7.3

* Dynamic on-resistance; see Figures 5 and 6

TP65H150LSG

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise stated.)

Symbol	Parameter	Limit Value	Unit	
V_{DSS}	Drain to source voltage ($T_J = -55^\circ\text{C}$ to 150°C)	650	V	
$V_{(TR)DSS}$	Transient drain to source voltage ^a	800		
V_{GSS}	Gate to source voltage	± 20		
P_D	Maximum power dissipation @ $T_c=25^\circ\text{C}$	69	W	
I_D	Continuous drain current @ $T_c=25^\circ\text{C}$ ^b	15	A	
	Continuous drain current @ $T_c=100^\circ\text{C}$ ^b	9.5	A	
I_{DM}	Pulsed drain current (pulse width: 10 μs)	60	A	
$(di/dt)_{RDMC}$	Reverse diode di/dt, repetitive ^c	1200	A/ μs	
$(di/dt)_{RDMT}$	Reverse diode di/dt, transient ^d	2400	A/ μs	
T_c	Operating temperature	Case	-55 to +150	$^\circ\text{C}$
T_J		Junction	-55 to +150	$^\circ\text{C}$
T_s	Storage temperature	-55 to +150	$^\circ\text{C}$	
T_{SOLD}	Soldering peak temperature ^e	260	$^\circ\text{C}$	

Notes:

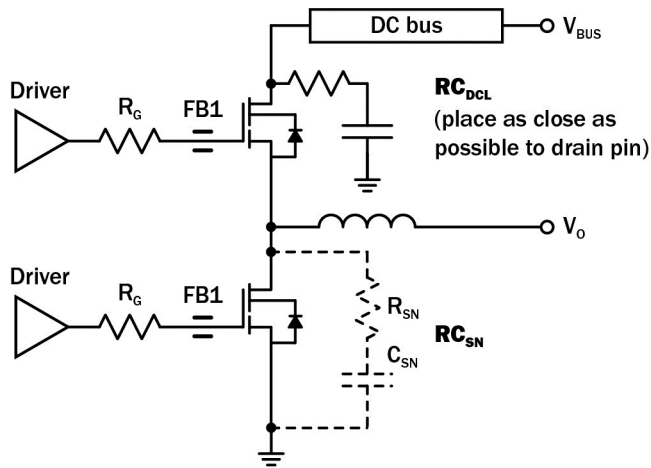
- In off-state, spike duty cycle $D < 0.01$, spike duration $< 1\mu\text{s}$
- For increased stability at high current operation, see Circuit Implementation on page 3
- Continuous switching operation
- ≤ 300 pulses per second for a total duration ≤ 20 minutes
- For 10 sec., 1.6mm from the case

Thermal Resistance

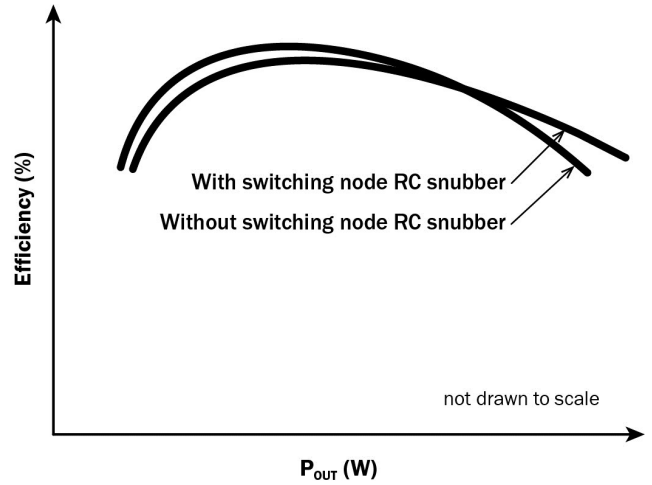
Symbol	Parameter	Maximum	Unit
$R_{\theta JC}$	Junction-to-case	1.8	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Junction-to-ambient ^f	62	$^\circ\text{C}/\text{W}$

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Circuit Implementation



Simplified Half-bridge Schematic



Efficiency vs Output Power

Recommended gate drive: (0V, 12V) with $R_{G(tot)} = 60\text{-}70\Omega$, where $R_{G(tot)} = R_G + R_{DRIVER}$

Gate Ferrite Bead (FB1)	Required DC Link RC Snubber (RC_{DCL}) ^a	Recommended Switching Node RC Snubber (RC_{SN}) ^{b, c}
240Ω@100MHz	4.7-10nF + 5Ω	22pF + 15Ω

Notes:

- RC_{DCL} should be placed as close as possible to the drain pin
- A switching node RC snubber (C, R) is recommended for high switching currents (>70% of I_{RDMC1} or I_{RDMC2} ; see page 5 for I_{RDMC1} and I_{RDMC2})
- I_{RDM} values can be increased by increasing R_G and C_{SN}

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Electrical Parameter (T_J=25 °C unless otherwise stated)

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
Forward Device Characteristics						
V _{(BL)DSS}	Drain-source voltage	650	—	—	V	V _{GS} =0V
V _{GS(th)}	Gate threshold voltage	3.3	4	4.8	V	V _{DS} =V _{GS} , I _D =0.5mA
R _{DS(on)eff}	Drain-source on-resistance ^a	—	150	180	mΩ	V _{GS} =10V, I _D =10A, T _J =25 °C
		—	307	—		V _{GS} =10V, I _D =10A, T _J =150 °C
I _{DSS}	Drain-to-source leakage current	—	2.5	25	μA	V _{DS} =650V, V _{GS} =0V, T _J =25 °C
		—	10	—		V _{DS} =650V, V _{GS} =0V, T _J =150 °C
I _{GSS}	Gate-to-source forward leakage current	—	—	100	nA	V _{GS} =20V
	Gate-to-source reverse leakage current	—	—	-100		V _{GS} =-20V
C _{ISS}	Input capacitance	—	576	—	pF	V _{GS} =0V, V _{DS} =400V, f=1MHz
C _{OSS}	Output capacitance	—	36	—		
C _{RSS}	Reverse transfer capacitance	—	2	—		
C _{O(er)}	Output capacitance, energy related ^b	—	55	—	pF	V _{GS} =0V, V _{DS} =0V to 400V
C _{O(tr)}	Output capacitance, time related ^c	—	103	—		
Q _G	Total gate charge	—	7.1	—	nC	V _{DS} =400V, V _{GS} =0V to 10V, I _D =10A
Q _{GS}	Gate-source charge	—	3.1	—		
Q _{GD}	Gate-drain charge	—	1	—		
Q _{OSS}	Output charge	—	41	—	nC	V _{GS} =0V, V _{DS} =0V to 400V
t _{D(on)}	Turn-on delay	—	27	—	ns	V _{DS} =400V, V _{GS} =0V to 12V, I _D =10A, R _G =65Ω, Z _{FB} =240Ω at 100MHz (See Figure 14)
t _R	Rise time	—	5.5	—		
t _{D(off)}	Turn-off delay	—	55	—		
t _F	Fall time	—	9.3	—		

Notes:

- Dynamic on-resistance; see Figures 17 and 18 for test circuit and conditions
- Equivalent capacitance to give same stored energy as V_{DS} rises from 0V to 400V
- Equivalent capacitance to give same charging time as V_{DS} rises from 0V to 400V

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Electrical Parameters (T_J=25 °C unless otherwise stated)

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
Reverse Device Characteristics						
I _S	Reverse current	—	—	9.5	A	V _{GS} =0V, T _C =100 °C, ≤20% duty cycle
V _{SD}	Reverse voltage ^a	—	1.9	—	V	V _{GS} =0V, I _S =10A
		—	1.3	—		V _{GS} =0V, I _S =5A
t _{RR}	Reverse recovery time	—	27	—	ns	I _S =10A, V _{DD} =400V, di/dt=1000A/ms
Q _{RR}	Reverse recovery charge	—	44	—	nC	
(di/dt) _{RDMC}	Reverse diode di/dt, repetitive ^b	—	—	1200	A/μs	
I _{RDMC1}	Reverse diode switching current, repetitive (dc) ^{c, e}	—	—	11	A	Circuit implementation and parameters on page 3
I _{RDMC2}	Reverse diode switching current, repetitive (ac) ^{c, e}	—	—	15	A	Circuit implementation and parameters on page 3
(di/dt) _{RDMT}	Reverse diode di/dt, transient ^d	—	—	2400	A/μs	
I _{RDMT}	Reverse diode switching current, transient ^{d, e}	—	—	18	A	Circuit implementation and parameters on page 3

Notes:

- Includes dynamic R_{DS(on)} effect
- Continuous switching operation
- Definitions: dc = dc-to-dc converter topologies; ac = inverter and PFC topologies, 50-60Hz line frequency
- ≤300 pulses per second for a total duration ≤20 minutes
- I_{RDM} values can be increased by increasing R_G and C_{SN} on page 3

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Typical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise stated)

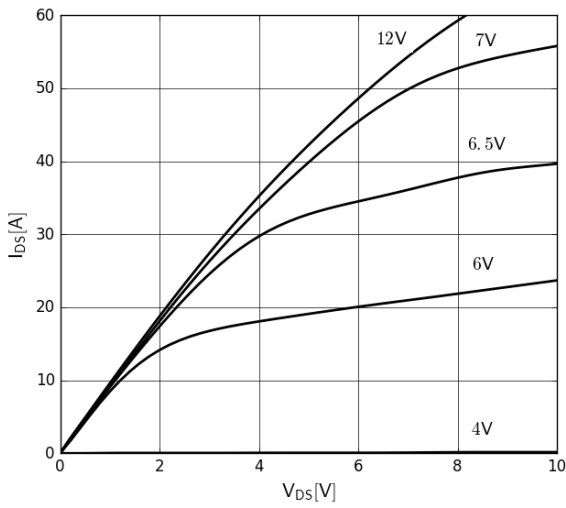


Figure 1. Typical Output Characteristics $T_J=25^\circ\text{C}$
Parameter: V_{GS}

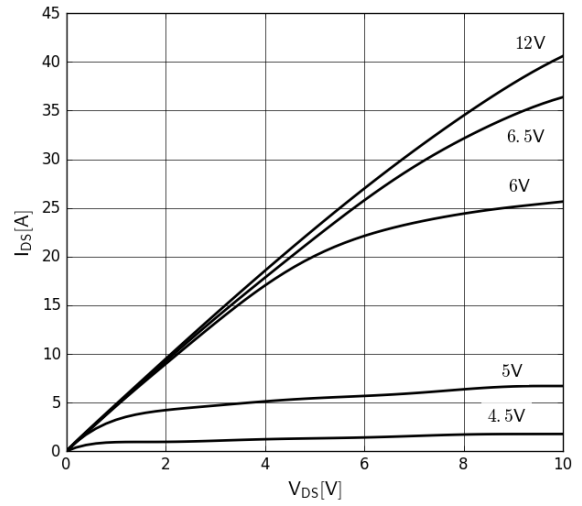


Figure 2. Typical Output Characteristics $T_J=150^\circ\text{C}$
Parameter: V_{GS}

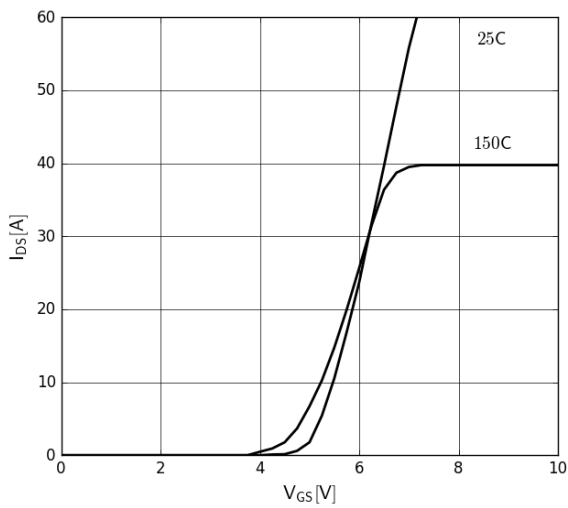


Figure 3. Typical Transfer Characteristics
 $V_{DS}=10\text{V}$, parameter: T_J

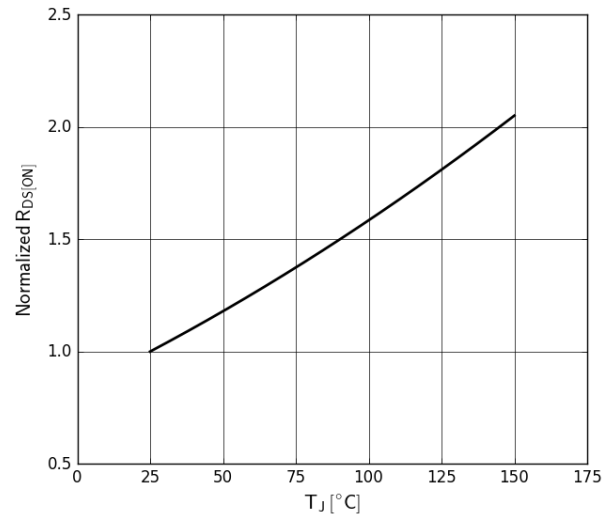


Figure 4. Normalized On-resistance
 $I_D=16\text{A}$, $V_{GS}=10\text{V}$

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Typical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise stated)

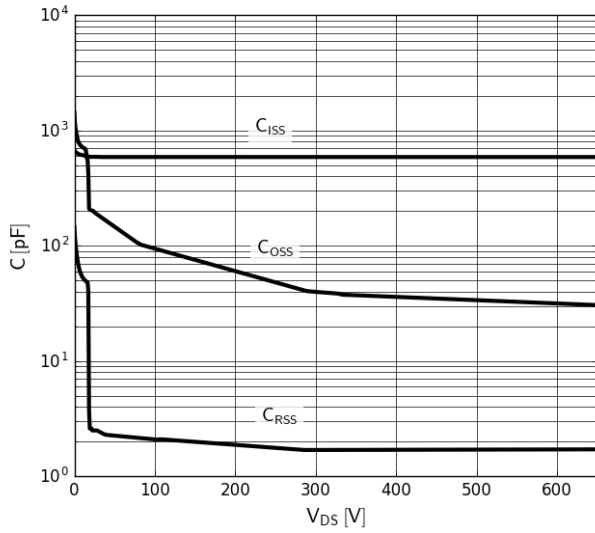


Figure 5. Typical Capacitance

$V_{GS}=0V, f=1MHz$

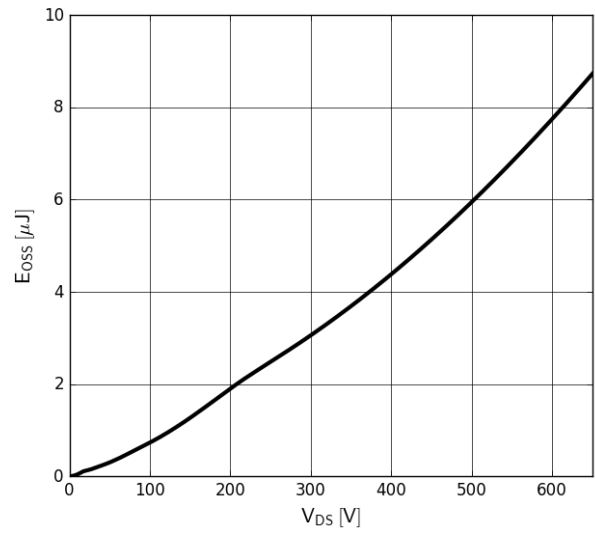


Figure 6. Typical C_{OSS} Stored Energy

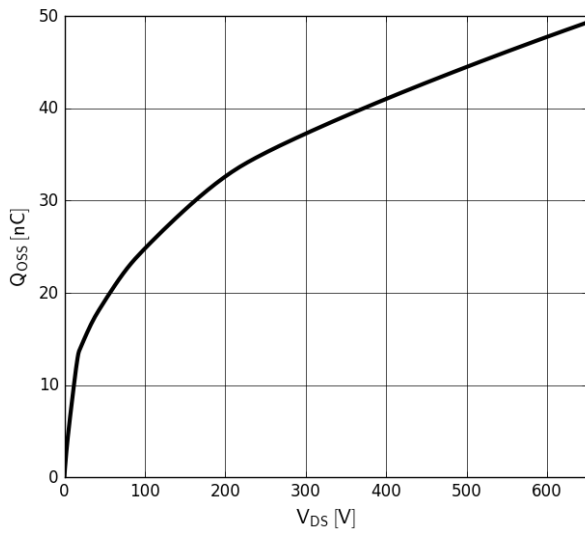


Figure 7. Typical Q_{OSS}

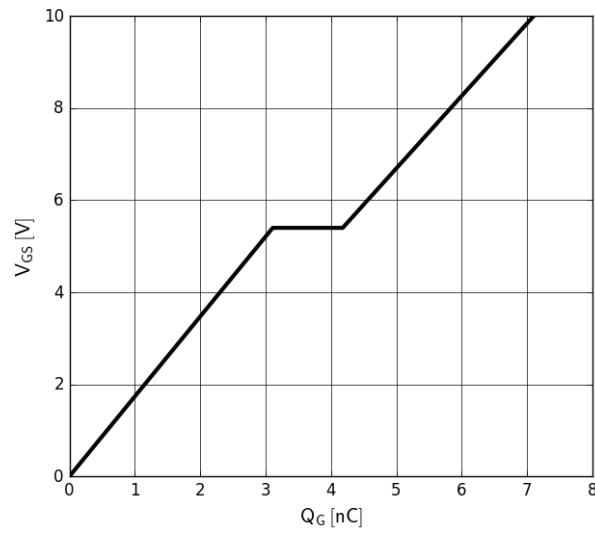


Figure 8. Typical Gate Charge

$I_{DS}=10A, V_{DS}=400V$

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Typical Characteristics ($T_c=25^\circ\text{C}$ unless otherwise stated)

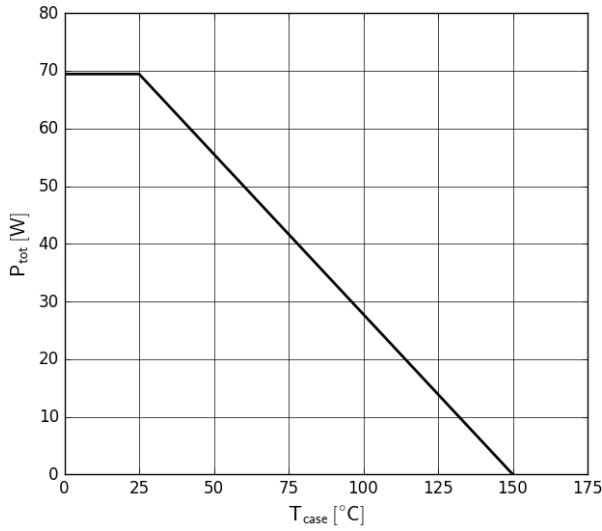


Figure 9. Power Dissipation

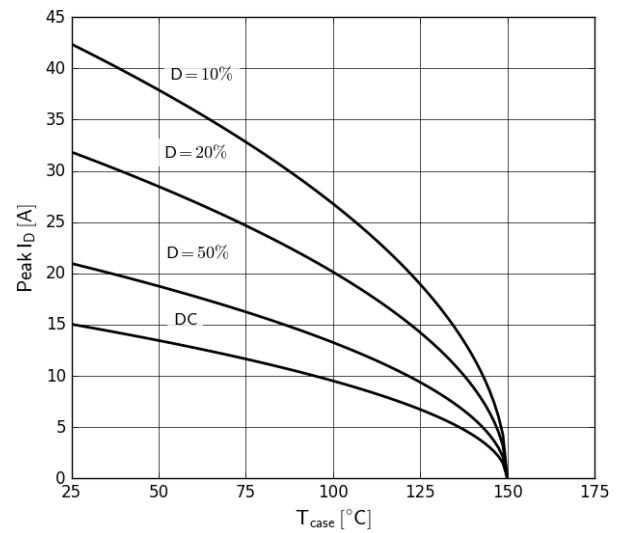


Figure 10. Current Derating
Pulse width $\leq 10\mu\text{s}$, $V_{GS} \geq 10\text{V}$

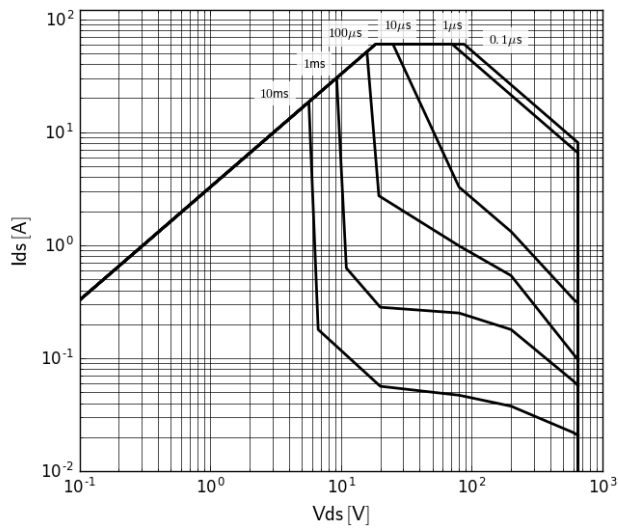


Figure 11. Safe Operating Area $T_c=25^\circ\text{C}$

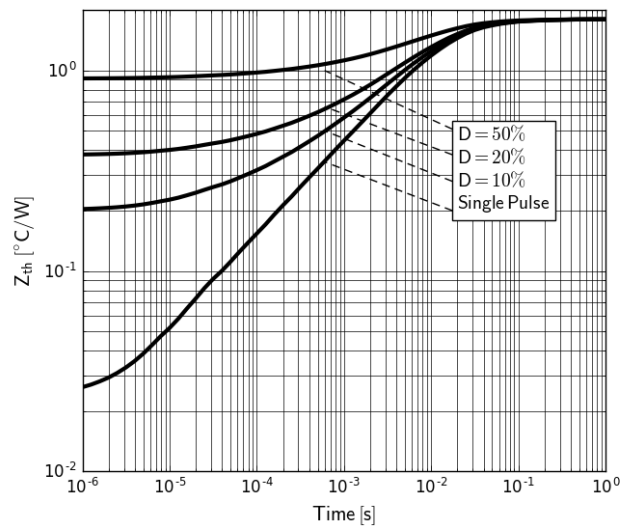


Figure 12. Transient Thermal Resistance

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Typical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise stated)

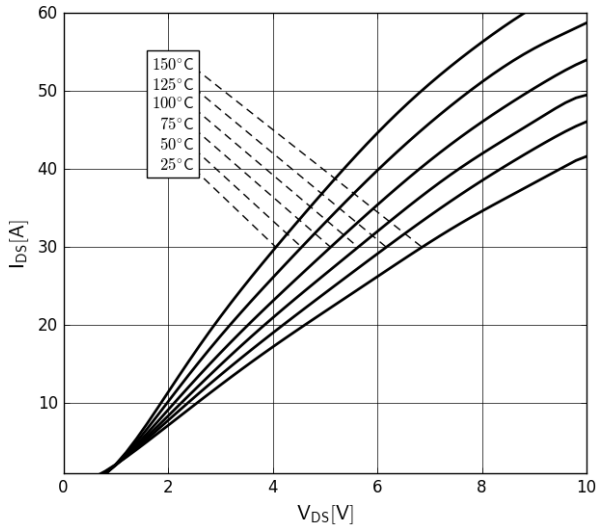


Figure 13. Forward Characteristics of Rev. Diode

$$I_S = f(V_{SD}), \text{ Parameter } T_J$$

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Test Circuits and Waveforms

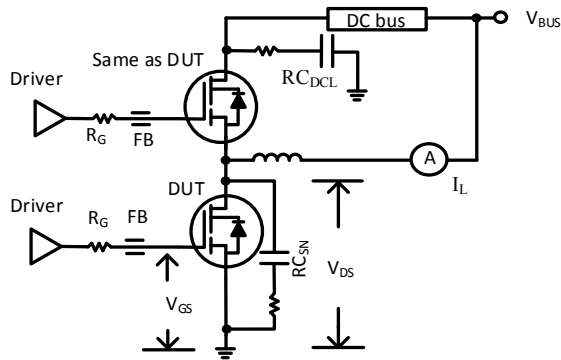


Figure 14. Switching Time Test Circuit
(see circuit implementation on page 3 for methods to ensure clean switching)

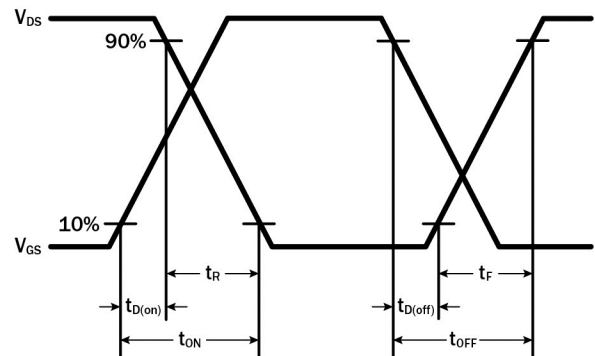


Figure 15. Switching Time Waveform

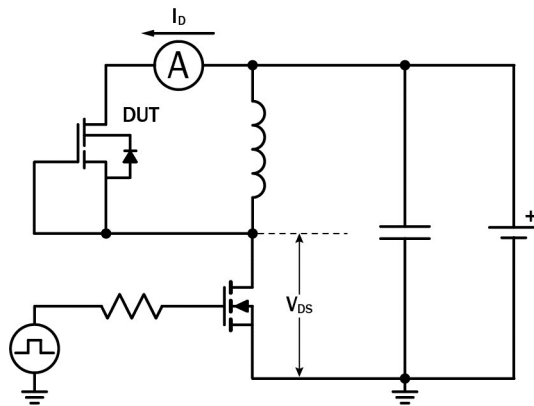


Figure 16. Diode Characteristics Test Circuit

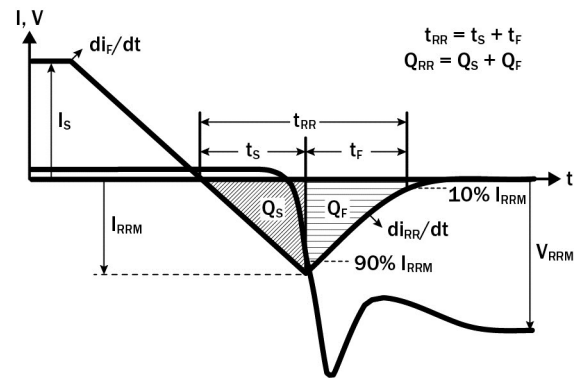


Figure 17. Diode Recovery Waveform

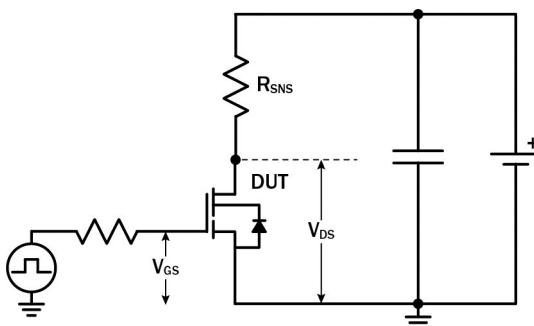


Figure 18. Dynamic $R_{DS(on)eff}$ Test Circuit

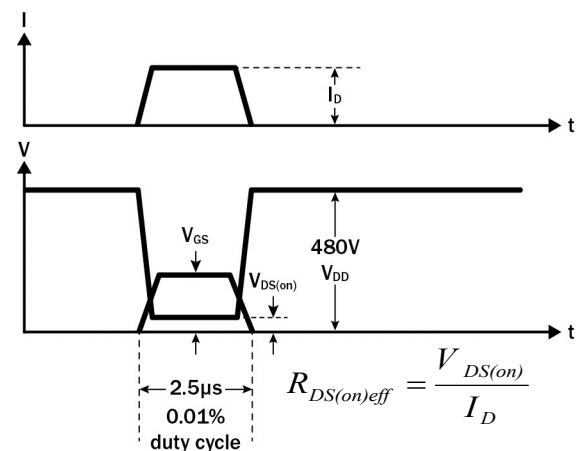


Figure 19. Dynamic $R_{DS(on)eff}$ Waveform

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Design Considerations

The fast switching of GaN devices reduces current-voltage crossover losses and enables high frequency operation while simultaneously achieving high efficiency. However, taking full advantage of the fast switching characteristics of GaN switches requires adherence to specific PCB layout guidelines and probing techniques.

Before evaluating Transphorm GaN devices, see application note [Printed Circuit Board Layout and Probing for GaN Power Switches](#). The table below provides some practical rules that should be followed during the evaluation.

When Evaluating Transphorm GaN Devices:

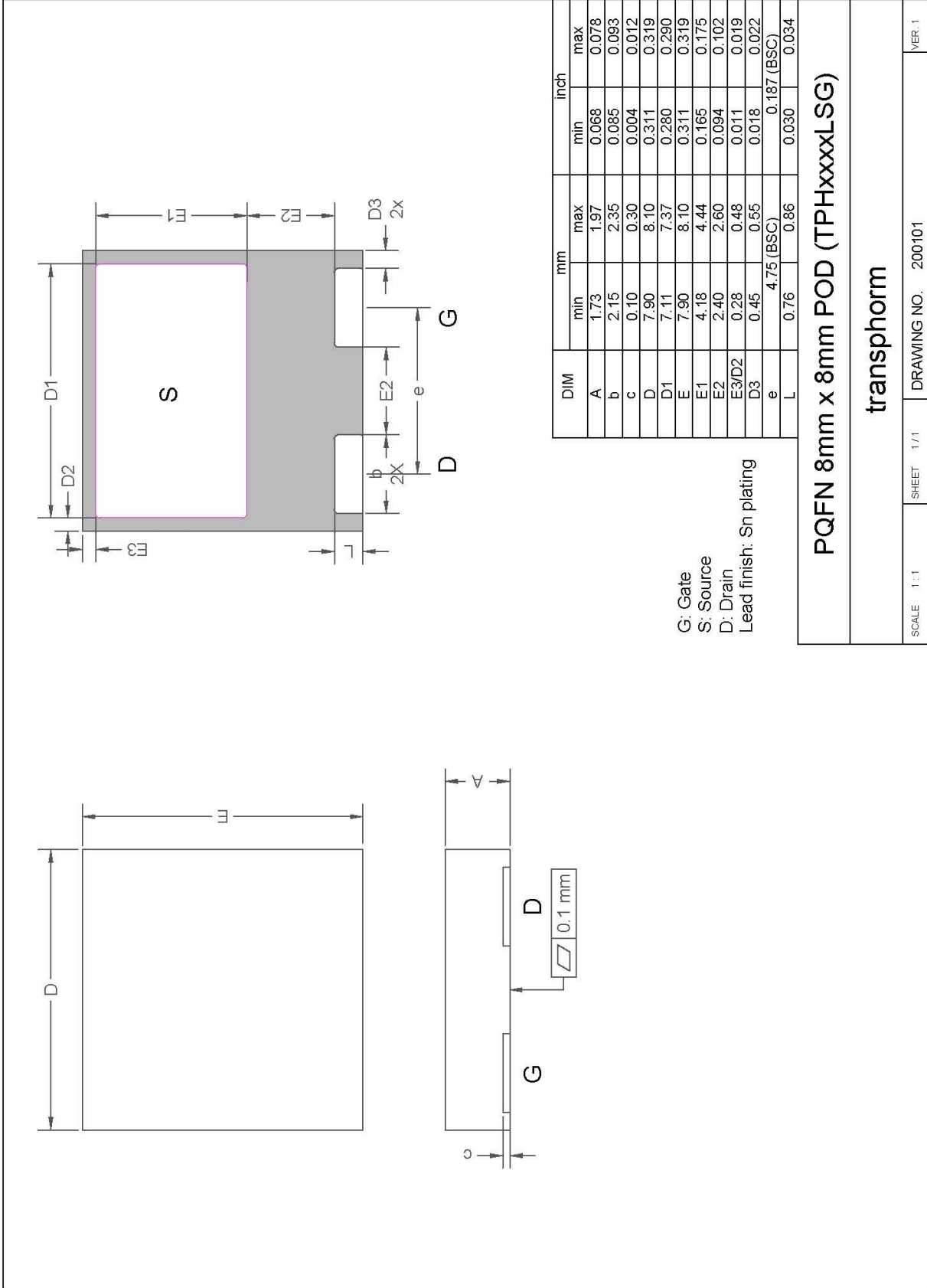
DO	DO NOT
Minimize circuit inductance by keeping traces short, both in the drive and power loop	Twist the pins of TO-220 or TO-247 to accommodate GDS board layout
Minimize lead length of TO-220 and TO-247 package when mounting to the PCB	Use long traces in drive circuit, long lead length of the devices
Use shortest sense loop for probing; attach the probe and its ground connection directly to the test points	Use differential mode probe or probe ground clip with long wire
See AN0003 : Printed Circuit Board Layout and Probing	

GaN Design Resources

The complete technical library of GaN design tools can be found at transphormusa.com/design:

- Reference designs
- Evaluation kits
- Application notes
- Design guides
- Simulation models
- Technical papers and presentations

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Revision History

Version	Date	Change(s)
0	2/14/2019	Preliminary Datasheet
1	8/15/2019	Complete datasheet